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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/873,537	06/04/2001	Carl J. Radens	FIS920000011US2(13312A)	4948	
. 75	05/21/2002				
SCULLY, SCOTT, MURPHY & PRESSER			EXAMINER		
400 Garden City			LEWIS, MONICA		
Garden City, N	Y 11530				
			ART UNIT	PAPER NUMBER	
			2822		
			DATE MAILED: 05/21/2002		

Please find below and/or attached an Office communication concerning this application or proceeding.

			N/w		
•	Application No.	Applicant(s)	Q.		
	09/873,537	RADENS ET AL.			
Office Action Summary	Examiner	Art Unit			
	Monica Lewis	2822			
The MAILING DATE of this communication appeared for Reply	opears on the cover shee	t with the correspondence address			
A SHORTENED STATUTORY PERIOD FOR REP THE MAILING DATE OF THIS COMMUNICATION  - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statu.  - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).  Status	l.  1.136(a). In no event, however, many  ply within the statutory minimum of  d will apply and will expire SIX (6)  ute, cause the application to becon	ay a reply be timely filed  of thirty (30) days will be considered timely.  MONTHS from the mailing date of this communication ne ABANDONED (35 U.S.C. § 133).	on.		
1) Responsive to communication(s) filed on 15	5 April 2002 .				
2a)⊠ This action is <b>FINAL</b> . 2b)□ T	This action is non-final.				
3) Since this application is in condition for allow closed in accordance with the practice under the practic			s is		
Disposition of Claims  4) ◯ Claim(s) 22-30 is/are pending in the application	tion				
4a) Of the above claim(s) is/are withdr					
5) Claim(s) is/are allowed.	awn nom consideration				
6)⊠ Claim(s) <u>22-30</u> is/are rejected.					
7) Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and	or election requirement				
Application Papers	·				
9) The specification is objected to by the Examiner.					
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.					
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
11) The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.					
If approved, corrected drawings are required in reply to this Office action.					
12) The oath or declaration is objected to by the E	examiner.				
Priority under 35 U.S.C. §§ 119 and 120					
13) Acknowledgment is made of a claim for forei	gn priority under 35 U.S	.C. § 119(a)-(d) or (f).			
a) All b) Some * c) None of:					
	1. Certified copies of the priority documents have been received.				
	2. Certified copies of the priority documents have been received in Application No				
<ul> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>					
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).					
<ul> <li>a)          The translation of the foreign language provisional application has been received.     </li> <li>15)          Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.     </li> </ul>					
Attachment(s)					
<ol> <li>Notice of References Cited (PTO-892)</li> <li>Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>Information Disclosure Statement(s) (PTO-1449) Paper No(s)</li> </ol>	5) 🔲 Notic	view Summary (PTO-413) Paper No(s) ce of Informal Patent Application (PTO-152) r:			

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## **DETAILED ACTION**

1. This office action is in response to the amendment filed April 15, 2002.

# Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims 22-27, 29 and 30 are rejected under 35 U.S.C. 103(a) as obvious over
- Chang (U.S. Patent No. 5,807,786) in view of Go et al. (U.S. Patent No. 5,592,016).

In regards to claim 22, Chang discloses the following:

- a) a substrate having a first level of electrically conductive features (See Column 2 Lines 54-59);
- b) a patterned anti-fuse dielectric layer (2) formed on said substrate, wherein said patterned anti-fuse dielectric layer includes an opening to at least one of said first level of electrically conductive features (See Figure 6);
- c) a patterned interlevel dielectric material (6) wherein said patterned interlevel dielectric includes vias (3), at léast one of said vias has a via space formed above said opening (See Figure 6); and
- d) a second level of electrically conductive features (5b) formed in said vias and via spaces (See Figure 6).

In regards to claim 23, Chang discloses the following:

a) substrate is composed of an interlevel dielectric material that is the same or different from said patterned interlevel dielectric material (See Column 2 Lines 54-59).

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In regards to claim 24, Chang discloses the following:

a) interlevel dielectric material is composed of an inorganic semiconductor material selected from the group consisting of Si0<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, diamond, diamond-like carbon and fluorinated doped oxides (See Column 3 Lines 44-47).

In regards to claim 25, Chang fails to disclose the following:

a) interlevel dielectric material is composed of an organic dielectric material selected from the group consisting of polyimides, polyamides, paralyene and polymethylmethacrylate.

However, Go et al. ("Go") discloses a semiconductor device where the dielectric material is composed of polyimides (See Column 4 Lines 39-48). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Chang to include a dielectric material composed of polyimides as disclosed in Go to resist abrasion.

In regards to claim 26, Chang discloses the following:

a) first and second levels of electrically conductive features are composed of the same or different conductive metal selected from the group consisting of aluminum, tungsten, copper, chromium, gold, platinum, palladium and alloys, mixtures and complexes thereof (See Column 4 Lines 59-64 and Column 3 Lines 36-38).

In regards to claim 27, Chang discloses the following:

a) anti-fuse dielectric layer is a dielectric material selected from the group consisting of Si0<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Si oxynitrides, amorphous Si, amorphous C, H-containing dielectrics, carbon, germanium, selenium, compound semiconductors, ceramics and anti-reflective coatings (See Column 3 Lines 9-10).

In regards to claim 29, Chang discloses the following:

a) interconnect level (10b) is formed over said patterned interlevel dielectric layer (See Figure 6).

In regards to claim 30, Chang discloses the following:

a) interconnect level includes a tapered metal contact region (See Figure 6).

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4. Claim 28 is rejected above under 35 U.S.C. 103(a) as obvious over Chang (U.S. Patent No. 5,807,786) in view of Go et al. (U.S. Patent No. 5,592,016) as applied to claims 22-27, 29 and 30 above, and further in view of McCollum et al. (U.S. Patent No. 5,770,885).

In regards to claim 28, Chang fails to disclose the following:

a) anti-reflective coating is silicon oxynitride.

However, McCollum et al. ("McCollum") discloses a semiconductor device where the anti-reflective coating is composed of silicon oxynitride (See Column 6 Lines 39-45). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Chang to include an anti-reflective coating of silicon oxynitride as disclosed in McCollum because it has a high dielectric constant which ultimately aids in reducing the leakage current while maintaining the same gate capacitance.

### Response to Arguments

- 5. Applicant's arguments filed April 15, 2002 have been fully considered but they are not persuasive. It is argued that "Chang does not disclose or suggest an anti-fuse layer with an opening which defines a via location." However, as indicated Chang discloses the following:
- a) a patterned anti-fuse dielectric layer (2) formed on said substrate, wherein said patterned anti-fuse dielectric layer includes an opening to at least one of said first level of electrically conductive features (See Figure 6); and
- b) a patterned interlevel dielectric material (6) wherein said patterned interlevel dielectric includes vias (3), at least one of said vias has a via space formed above said opening (See Figure 6).

Therefore, Chang discloses the limitations that Applicant stated were not present.

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6. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

#### Conclusion

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Monica Lewis whose telephone number is 703-305-3743. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr. can be reached on 703-308-4940. The fax phone number for the organization where this application or proceeding is assigned is 703-308-7722 for regular and after final communications. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

ML

May 17, 2002

CARL WHITEHEAD, JR.
SUPERVISORY PATENT EXAMINES:

TECHNOLOGY CENTER 2800